Low-Voltage CMOS Quad 2-Input OR Gate

With 5 V–Tolerant Inputs

The 74LVC32A is a high performance, quad 2–input OR gate operating from a 1.2 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows 74LVC32A inputs to be safely driven from 5.0 V devices.

Current drive capability is 24 mA at the outputs.

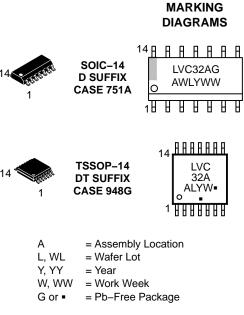
Features

- Designed for 1.2 V to 3.6 V V_{CC} Operation
- 5.0 V Tolerant Inputs Interface Capability With 5.0 V TTL Logic
- 24 mA Output Sink and Source Capability
- Near Zero Static Supply Current (10 µA) Substantially Reduces System Power Requirements
- ESD Performance: Human Body Model >2000 V Machine Model >200 V
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



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(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

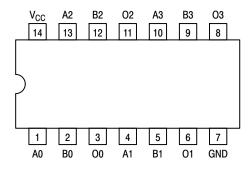
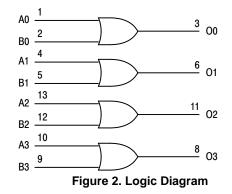


Figure 1. Pinout: 14-Lead (Top View)

PIN NAMES

Pins	Function
An, Bn	Data Inputs
On	Outputs



TRUTH TABLE

Inputs		Outputs
An	Bn	On
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

H = High Voltage Level L = Low Voltage Level

For $I_{\mbox{\scriptsize CC}}$ reasons, DO NOT FLOAT Inputs

MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +6.5		V
VI	DC Input Voltage	$-0.5 \le V_{I} \le +6.5$		V
V _O	DC Output Voltage	$-0.5 \le V_{O} \le V_{CC} + 0.5$	Output in HIGH or LOW State (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
Ι _{ΟΚ}	DC Output Diode Current	-50	V _O < GND	mA
		+50	$V_{O} > V_{CC}$	mA
Ι _Ο	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C
ΤL	Lead Temperature, 1 mm from Case for 10 Seconds	T _L = 260		°C
TJ	Junction Temperature Under Bias	T _J = 135		°C
θ_{JA}	Thermal Resistance (Note 2)	SOIC = 85 TSSOP = 100		°C/W
MSL	Moisture Sensitivity		Level 1	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
1. I_O absolute maximum rating must be observed.
2. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Units
V _{CC}	Supply Voltage Operating Functional	1.65 1.2		3.6 3.6	V
VI	Input Voltage	0		5.5	V
V _O	Output Voltage HIGH or LOW State 3–State	0 0		V _{CC} 5.5	V
I _{ОН}	$ HIGH Level Output Current \\ V_{CC} = 3.0 \ V - 3.6 \ V \\ V_{CC} = 2.7 \ V - 3.0 \ V $			-24 -12	mA
I _{OL}	$ LOW Level Output Current \\ V_{CC} = 3.0 V - 3.6 V \\ V_{CC} = 2.7 V - 3.0 V $			24 12	mA
T _A	Operating Free–Air Temperature	-40		+125	°C
Δt/ΔV	Input Transition Rise or Fall Rate $V_{CC} = 1.65 \text{ V to } 2.7 \text{ V}$ $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	0 0		20 10	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

		−40°C to +85°C			5°C	–40°C to +125°C			
Symbol	Parameter	Conditions	Min	Typ (Note 3)	Max	Min	Typ (Note 3)	Max	Unit
VIH	HIGH-level input	V _{CC} = 1.2 V	1.08	-	-	1.08	-	_	V
	voltage	V _{CC} = 1.65 V to 1.95 V	0.65 x V _{CC}	-	-	0.65 x V _{CC}	-	-	
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	_	
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	_	
VIL	LOW-level input	V _{CC} = 1.2 V	-	-	0.12	-	-	0.12	V
	voltage	V _{CC} = 1.65 V to 1.95 V	-	-	0.35 x V _{CC}	-	-	0.35 x V _{CC}	
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	-	0.7	
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	-	0.8	
V _{OH}	HIGH-level output	$V_{I} = V_{IH}$ (or V _{IL}						V
	voltage	$I_{O} = -100 \ \mu\text{A};$ $V_{CC} = 1.65 \ \text{V} \text{ to } 3.6 \ \text{V}$	V _{CC} - 0.2	-	_	V _{CC} – 0.3	-	-	
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	1.05	-	-	
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.8	-	-	1.65	-	-	
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	2.05	-	-	
		$I_{O} = -18$ mA; $V_{CC} = 3.0$ V	2.4	-	-	2.25	-	-	
		$I_{O} = -24$ mA; $V_{CC} = 3.0$ V	2.2	-	-	2.0	-	-	
VOL	LOW-level output	$V_{I} = V_{IH}$ (or V _{IL}						V
	voltage	$I_O = 100 \ \mu\text{A};$ V _{CC} = 1.65 V to 3.6 V	-	-	0.2	-	-	0.3	
		I _O = 4 mA; V _{CC} = 1.65 V	-	-	0.45	-	-	0.65	
		$I_{O} = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.6	-	-	0.8	
		$I_0 = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.4	-	-	0.6	
		$I_0 = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	-	0.8	
lı	Input leakage current	V_{I} = 5.5V or GND V_{CC} = 3.6 V	-	±0.1	±5	-	±0.1	±20	μA
I _{OFF}	Power-off leakage current	V _I or V _O = 5.5 V; V _{CC} = 0.0 V	_	±0.1	±10	_	±0.1	±20	μA
I _{CC}	Supply current	$V_{I} = V_{CC} \text{ or GND; } I_{O} = 0 \text{ A;}$ $V_{CC} = 3.6 \text{ V}$	Ι	0.1	10	_	0.1	40	μA
ΔI_{CC}	Additional supply current	per input pin; $V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A};$ $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	_	5	500	-	5	5000	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. All typical values are measured at $T_A = 25^{\circ}C$ and $V_{CC} = 3.3$ V, unless stated otherwise.

AC ELECTRICAL CHARACTERISTICS (t_R = t_F = 2.5 ns)

			–40°C to +85°C		–40°C to +125°C				
Symbol	Parameter	Conditions	Min	Typ1	Max	Min	Typ1	Max	Unit
t _{pd}	Propagation Delay (Note 5)	V _{CC} = 1.2 V	-	10.0	-	-	-	-	ns
		V_{CC} = 1.65 V to 1.95 V	0.5	4.2	9.0	0.5	-	10.4	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	2.4	4.9	1.0	-	5.7	
		V _{CC} = 2.7 V	1.0	2.5	4.4	1.0	-	5.5	
		V_{CC} = 3.0 V to 3.6 V	1.0	2.2	3.8	1.0	-	5.0	
t _{sk(0)}	Output Skew Time (Note 6)	V_{CC} = 3.0 V to 3.6 V	-	-	1.0	-	-	1.5	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Typical values are measured at $TA = 25^{\circ}C$ and Vcc = 3.3 V, unless stated otherwise.

 t_{pd} is the same as t_{PLL} and t_{PLL}.
 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (toshL) or LOW-to-HIGH (tosLH); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C			
Symbol	Characteristic	Condition	Min	Тур	Мах	Unit
V _{OLP}	Dynamic LOW Peak Voltage (Note 7)			0.8 0.6		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 7)			-0.8 -0.6		V

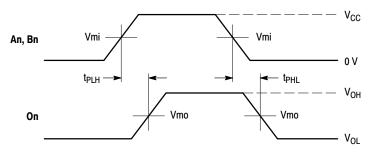
7. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
CIN	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	4.0	pF
Соит	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	5.0	pF
C _{PD}	Power Dissipation Capacitance	Per input; $V_I = GND$ or V_{CC}		
	(Note 8)	V_{CC} = 1.65 V to 1.95 V	4.7	
		V_{CC} = 2.3 V to 2.7 V	8.0	
		V_{CC} = 3.0 V to 3.6 V	11.0	

8. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W). P_D = C_{PD} x V_{CC}² x fi x N + Σ (C_L x V_{CC}² x fo) where: fi = input frequency in MHz; fo = output frequency in MHz C_L = output load capacitance in pF V_{CC} = supply voltage in Volts

N = number of outputs switching $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

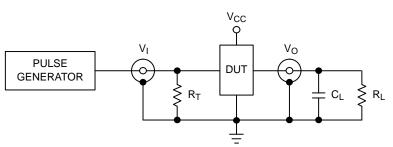


WAVEFORM 1 - PROPAGATION DELAYS

 t_{R} = t_{F} = 2.5 ns, 10% to 90%; f = 1 MHz; t_{W} = 500 ns

	Vcc					
Symbol	3.3 V <u>+</u> 0.3 V	2.7 V	V _{CC} < 2.7 V			
Vmi	1.5 V	1.5 V	Vcc/2			
Vmo	1.5 V	1.5 V	Vcc/2			

Figure 3. AC Waveforms



 C_L includes jig and probe capacitance R_T = Z_{OUT} of pulse generator (typically 50 $\Omega)$

Supply Voltage	Input		Lo	ad
V _{CC} (V)	VI	t _r , t _f	C∟	RL
1.2	V _{CC}	≤ 2 ns	30 pF	1 kΩ
1.65 – 1.95	V _{CC}	≤ 2 ns	30 pF	1 kΩ
2.3 – 2.7	V _{CC}	≤ 2 ns	30 pF	500 Ω
2.7	2.7 V	\leq 2.5 ns	50 pF	500 Ω
3 – 3.6	2.7 V	≤ 2.5 ns	50 pF	500 Ω

Figure 4. Test Circuit

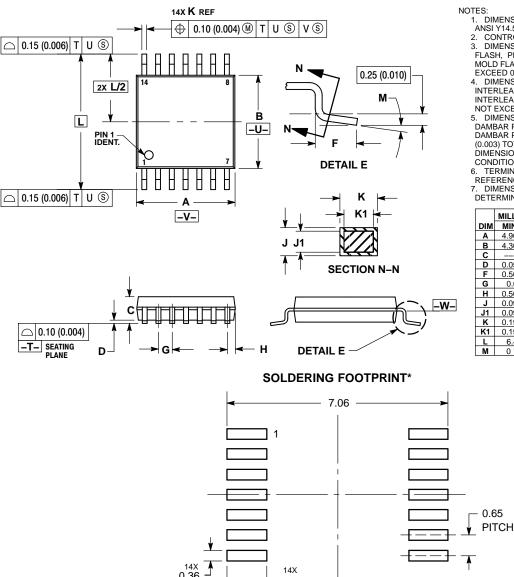
ORDERING INFORMATION

Device	Package	Shipping [†]
74LVC32ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
74LVC32ADTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G **ISSUE B**



14X 0.36

details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

*For additional information on our Pb-Free strategy and soldering

DIMENSIONS: MILLIMETERS

14X 1.26 DIES.
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE

EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION

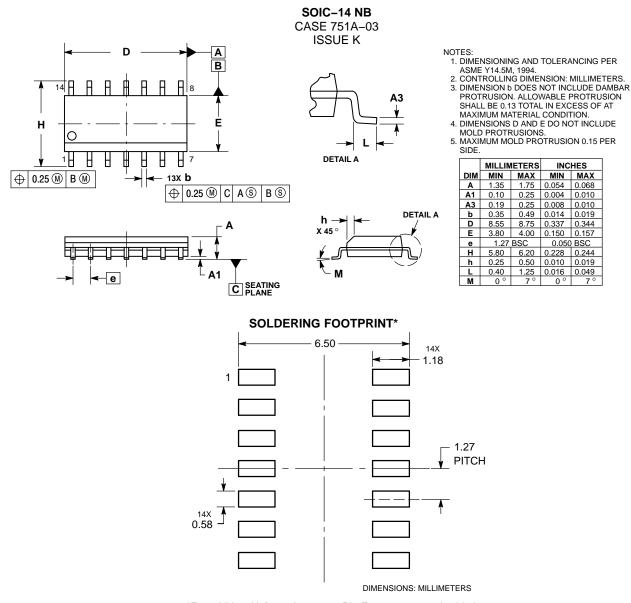
CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR

REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252	2 BSC	
М	0 °	8 °	0 °	8 °	

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PACKAGE DIMENSIONS



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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